

BUX80

High-reliability discrete products and engineering services since 1977

HIGH VOLTAGE NPN TRANSISTOR

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	BUX80	Unit
Collector-emitter voltage	V _{CEO}	400	V
Collector-emitter voltage (V _{BE} = 0)	V _{CES}	800	V
Emitter-base voltage	V _{EBO}	10	V
Collector current – Continuous -Peak	lc	10 15	А
Base current – continuous	IB	5.0	А
Total power dissipation @ T c = 25°C Derate above 25°C	PD	100 0.8	₩ ₩/°C
Operating and storage temperature range	T _J , T _{stg}	-65 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	Rejc	1.25	°C/W

ELECTRICAL CHARACTERISTICS (T_c = 25°C unless otherwise noted)

	Characteristics	Symbol	Minimum	Maximum	Unit
OFF CHARACTERISTICS					
Collector-emitter (I _c = 100mA, I _B = 0	sustaining voltage (1) , L = 25mH)	V _{CEO(sus)}	400	-	V
COLLECTOR-CUTO $(V_{CE} = 800V, V_{BE} = 0)$ $(V_{CE} = 800V, V_{BE} = 0)$	0)	Ices	-	1.0 3.0	mA
Emitter cutoff cur $(V_{EB} = 10V, I_C = 0)$	rent	Гево	-	10	mA
ON CHARACTERIS	TICS				
DC current gain $(I_C = 1.2A, V_{CE} = 5.0)$)V)	h _{FE}	30(typ)		
Collector-emitter ($I_{c} = 5.0A$, $I_{B} = 1.0A$ ($I_{c} = 8.0A$, $I_{B} = 2.5A$		$V_{CE(sat)}$	-	1.5 3.0	V
Base-emitter satu (I _c = 5.0A, I _B = 1.0A (I _c = 8.0A, I _B = 2.5A	A)	V _{BE(sat)}		1.4 1.8	v
SWITCHING CHARACTERISTICS					
Turn on time	V _{cc} = 250V, I _c = 5.0A,	t _{on}	-	0.5	μs
Storage time	I _{B1} = 1.0A, I _{B2} = -2.0A	ts	-	3.5	μs
Fall time		tr	-	0.5	μs

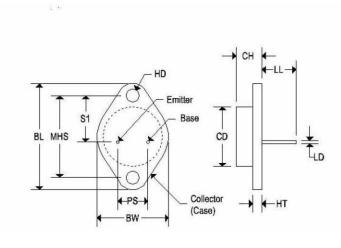
Note 1: Pulse test: pulse width = 300 μ s, duty cycle \leq 2.0%.



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MECHANICAL CHARACTERISTICS

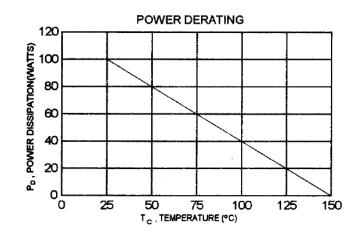
Case:	DO-35
Marking:	Body painted, alpha-numeric
Polarity:	Cathode band



B	U	X8	0
	U	no	U

HIGH VOLTAGE NPN TRANSISTOR

	TO-3			
	Inches		Millim	neters
	Min	Мах	Min	Max
CD	-	0.875		22.220
CH	0.250	0.380	6.860	9.650
HT	0.060	0.135	1.520	3.430
BW		1.050	÷	26.670
HD	0.131	0.188	3.330	4.780
LD	0.038	0.043	0.970	1.090
LL	0.312	0.500	7.920	12.700
BL	1.550	REF	39.37	0 REF
MHS	1.177	1.197	29.900	30.400
PS	0.420	0.440	10.670	11.180
S1	0.655	0.675	16.640	17.150

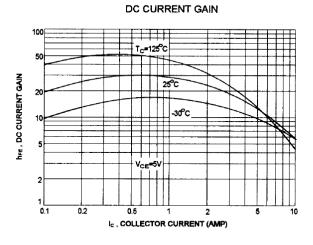




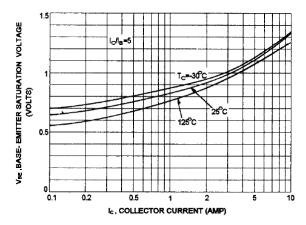
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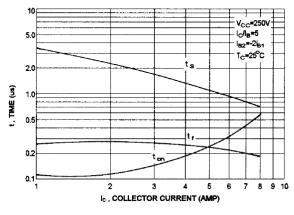
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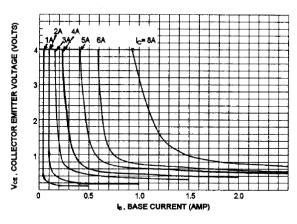
BASE-EMITTER SATURATION VOLTAGE



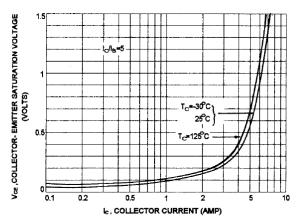




COLLECTOR SATURATION REGION



COLLECTOR-EMITTER SATURATION VOLTAGE



SAFE OPERATING AREA

